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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	18	etch\$3 and (indium adj phosphide) and ("BCl sub 3" pr trichloride) and ("H.sub 2" or hydrogen) and ("HBr" or (hydrogen adj bromide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OK		2005/07/14 14:10

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
ij	7145	(438/700.ccls. or 438/706.ccls. or 438/710.ccls. or 438/712.ccls. or 438/718.ccls. or 438/719.ccls. or 438/720.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:16
L2	370	L1 and (wafer\$1 or substrate\$1) and (((front near3 surface) same (back or rear or bottom or backside)) or ((first near3 surface) same (second near3 surface)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:16
13	170	L2 and ((hole\$1 or via or opening\$1) with through)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:17
L4	100401	(wafer\$1 or substrate\$1) and (((front near3 surface) same (back or rear or bottom or backside)) or ((first near3 surface) same (second near3 surface)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:19
L5	52673	L4 and (((front near3 surface) with (wafer or substrate)) or ((first near3 surface) with (wafer or substrate)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:19
L6	8816	L5 and ((plasma or dry) same etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:19
L7	7153	L6 and ((((back or backside) near3 surface) with (wafer or substrate)) or ((second near3 surface) with (wafer or substrate)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:19
L8	1922	L7 and ((hole\$1 or via or opening\$1) with (((back or backside) near3 surface) or (second near3 surface)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:19
L9	1535	L8 and ((hole\$1 or via or opening\$1) with through)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:19

L10	939	L9 and ((((back or backside) near3 surface) or (second near3 surface)) with through)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:19
UI	930	L10 and ((form\$5 or generat\$3 or produc\$3 or mak\$3 or creat\$3 or fabricat\$3 or etch\$3) with (hole\$1 or via or opening\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:19
L12	55	L11 and (bak\$3 with (resist\$1 or photoresist\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:19
L13	5 9	L11 and (heat\$3 with (resist\$1 or photoresist\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:19
L14	103	L12 or L13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:19
L15	182	L11 and ((photoresist or resist) with ((backside or back or lower or second) near3 surface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:21
L16	166	L3 not L14 not L15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/14 15:21